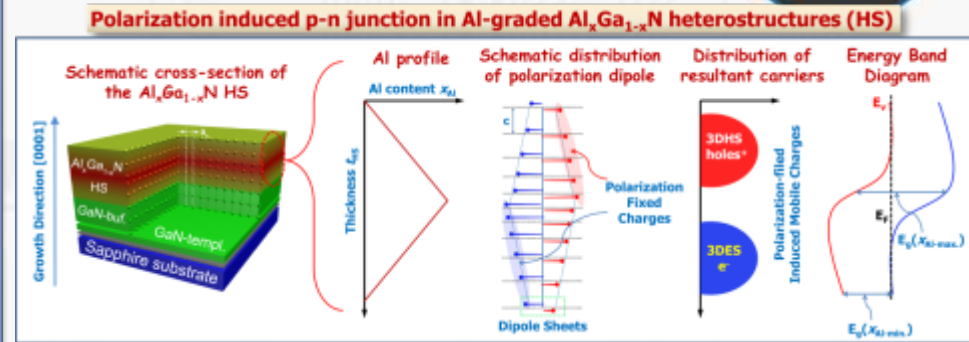


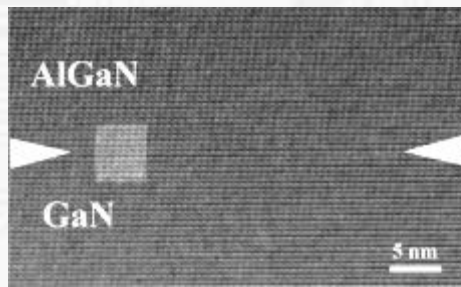


- GaN, AlN, and InN growth and characterization
- Novel wide bandgap device fabrication
- GaN Devices from Fundamental Materials

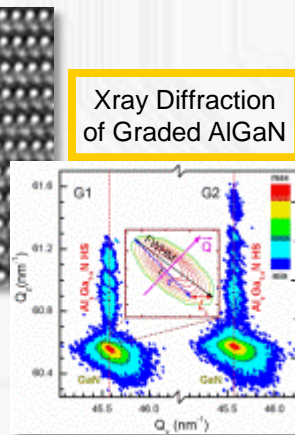


Novel Devices

Growth and Characterization



Transmission Electron Microscopy of Epitaxial AlGaIn



GaN Devices from Fundamental Materials

Polarization doped pn-junction shows classical diode I-V response similar to impurity doped pn-junction.

